



# **RF ESD Protection Diodes**

- ESD protection of RF antenna / interfaces or ultra high speed data lines acc. to: IEC61000-4-2 (ESD): ± 15 KV (air / contact) IEC61000-4-4 (EPT): 40 A (5/50 ns) IEC61000-4-5 (surge): 5 A (8/20 μs)
- Very low line capacitance: 0.4 pF @ 1 GHz ( 0.2 pF per diode)
- Ultra low series inductance: 0.4 nH per diode
- Very low clamping voltage
- Ultra small leadless package:1.2 x 0.8 x 0.39 mm<sup>3</sup>
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

### Applications in anti-parallel configuration

 For low RF signal levels without superimposed DC voltage: e.g. GPS, XM-Radio, Sirius, DVB, DMB, DAB, Remote Keyless Entry

#### Applications in rail-to-rail configuration

• For high RF signal levels or low RF signal levels with superimposed DC voltage: e.g. HDMI, S-ATA, Gbit Ethernet



#### ESD0P4RFL



Туре	Package	Configuration	Marking
ESD0P4RFL	TSLP-4-7	anti-parallel	E4





# **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit				
ESD contact discharge <sup>1)</sup>	V <sub>ESD</sub>	15	kV				
Peak pulse current ( $t_p = 8 / 20 \ \mu s$ ) <sup>2)</sup>	I <sub>pp</sub>	5	А				
Operating temperature range	T <sub>op</sub>	-55150	°C				
Storage temperature	T <sub>stg</sub>	-65150					

# **Electrical Characteristics** at $T_A = 25^{\circ}C$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	]
Characteristics -					
Reverse working voltage <sup>3)</sup>	V <sub>RWM</sub>	-	-	50	V
Reverse current <sup>3)</sup>	I <sub>R</sub>	-	20	100	nA
<i>V</i> <sub>R</sub> = 50 V					
Forward clamping voltage <sup>2)</sup>	V <sub>FC</sub>	-	6	9	V
I <sub>PP</sub> = 5 A					
Diode capacitance <sup>4)</sup>	CT	-	0.4	-	pF
<i>V</i> <sub>R</sub> = 0 V, <i>f</i> = 1 GHz					
Series inductance per diode	L <sub>S</sub>	-	0.4	-	nH

<sup>1</sup>V<sub>ESD</sub> according to IEC61000-4-2, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

 $^{2}I_{pp}$  according to IEC61000-4-5, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

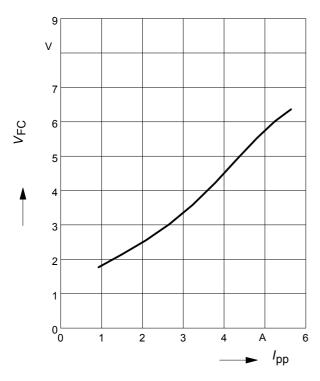
<sup>3</sup>Only valid in rail-to-rail configuration with  $V_{CC} \le V_{RWM}$ 

<sup>4</sup>Total capacitance line to ground (2 diodes in parallel)



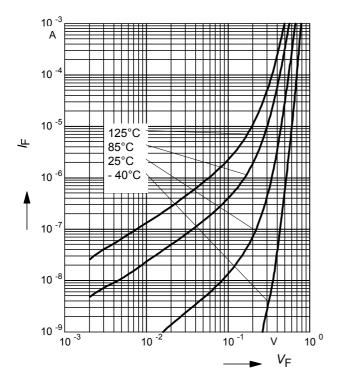
# Forward clamping voltage $V_{FC} = f(I_{PP})$

 $t_{\rm p}$  = 8 / 20 µs



# Forward current $I_{\rm F}$ = $f(V_{\rm F})$

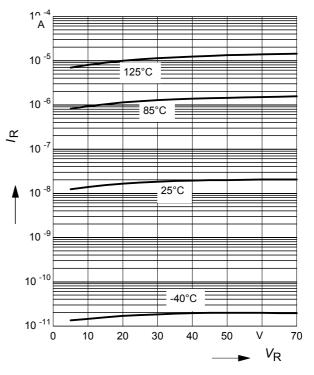
leakage in anti-parallel configuration



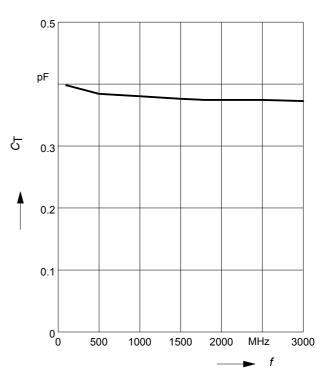
# **Reverse current** $I_{R} = f(V_{R})$

 $T_A$  = Parameter

leakage in rail-to-rail configuration



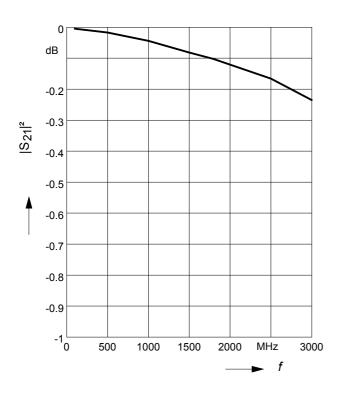
Line capacitance  $C_{T} = f$  (f)  $V_{R} = 0 V$ 







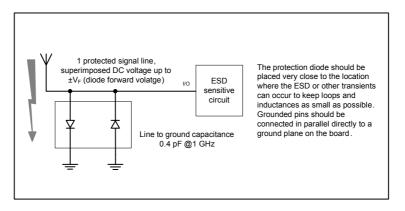
# $Insertion \ loss \ l_L = -|S_{21}|^2 = f(f) \\ V_{\mathsf{R}} = 0 \ \mathsf{V}, \ Z = 50 \ \Omega$





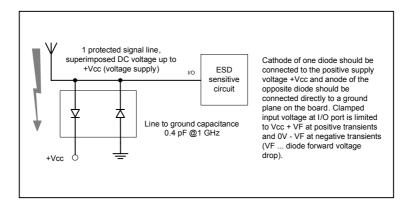
## 1. Application example ESD0P4RFL

1 RF signal channel, anti-parallel configuration

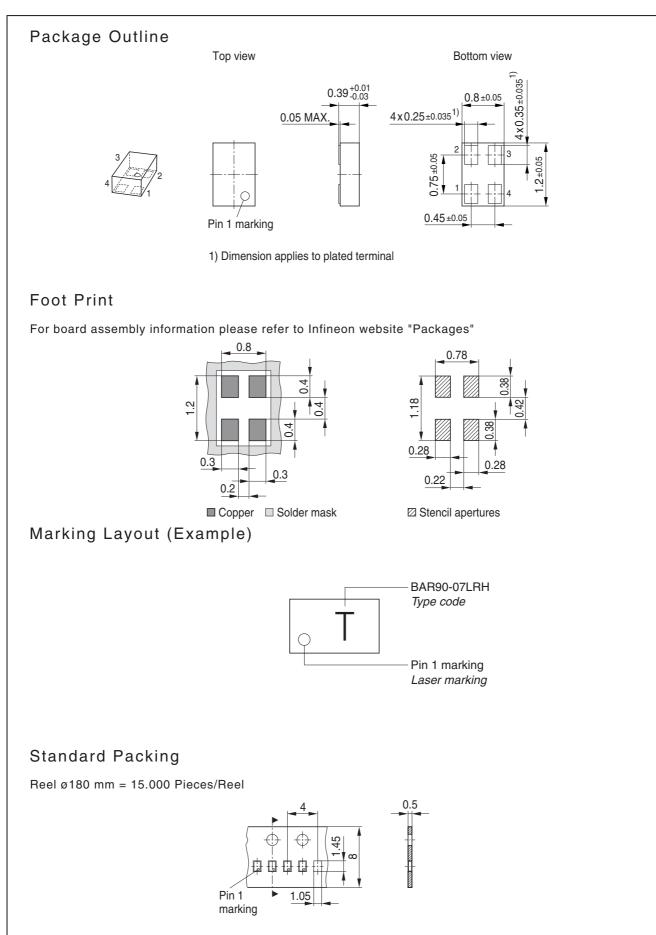


### 2. Application example ESD0P4RFL

1 RF signal channel, rail-to-rail configuration









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